

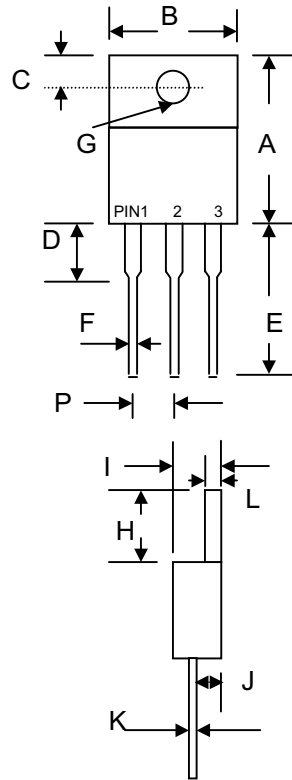
**Data Sheet 2656 Rev.—**

**Features**

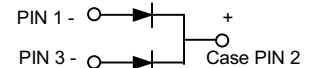
- Glass Passivated Die Construction
- Super-Fast Switching for High Efficiency
- High Current Capability
- Low Reverse Leakage Current
- High Surge Current Capability
- Plastic Material has UL Flammability Classification 94V-O

**Mechanical Data**

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: See Diagram
- Weight: 2.24 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



| TO-220                      |               |               |
|-----------------------------|---------------|---------------|
| Dim                         | Min           | Max           |
| A                           | 0.587(14.9)   | 0.595(15.10)  |
| B                           | —             | 0.413(10.50)  |
| C                           | 0.103(2.62)   | 0.113(2.87)   |
| D                           | 0.140(3.56)   | 0.160(4.06)   |
| E                           | 0.530(13.46)  | 0.560(14.22)  |
| F                           | 0.027(0.68)   | 0.037(0.94)   |
| G                           | 0.147(3.74) Ø | 0.154(3.91) Ø |
| H                           | 0.230(5.84)   | 0.270(6.86)   |
| I                           | 0.175(4.44)   | 0.185(4.70)   |
| J                           | 0.100(2.54)   | 0.110(2.79)   |
| K                           | 0.014(0.35)   | 0.025(0.64)   |
| L                           | 0.045(1.14)   | 0/055(1.40)   |
| P                           | 0.095(2.41)   | 0.105(2.67)   |
| All Dimensions in inch( mm) |               |               |



**Maximum Ratings and Electrical Characteristics @T<sub>A</sub>=25°C unless otherwise specified**

Single Phase, half wave, 60Hz, resistive or inductive load.  
For capacitive load, derate current by 20%.

| Characteristic  | Symbol                            | FEP 16AT    | FEP 16BT | FEP 16CT | FEP 16DT | FEP 16FT | FEP 16GT | FEP 16JT | Unit |
|---|-----------------------------------|-------------|----------|----------|----------|----------|----------|----------|------|
| Peak Repetitive Reverse Voltage   | V <sub>RRM</sub>                  | 50          | 100      | 150      | 200      | 300      | 400      | 600      | V    |
| Working Peak Reverse Voltage  | V <sub>VRWM</sub>                 |             |          |          |          |          |          |          |      |
| DC Blocking Voltage   | V <sub>R</sub>                    |             |          |          |          |          |          |          |      |
| RMS Reverse Voltage   | V <sub>R(RMS)</sub>               | 35          | 70       | 105      | 140      | 210      | 280      | 420      | V    |
| Average Rectified Output Current @T <sub>C</sub> = 105°C  | I <sub>o</sub>                    | 16          |          |          |          |          |          |          | A    |
| Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method) | I <sub>FSM</sub>                  | 125         |          |          |          |          |          |          | A    |
| Forward Voltage @I <sub>F</sub> = 8.0A  | V <sub>FM</sub>                   | 0.95        |          |          | 1.3      |          | 1.7      |          | V    |
| Peak Reverse Current @T <sub>A</sub> = 25°C   | I <sub>RM</sub>                   | 10          |          |          |          |          |          |          | µA   |
| At Rated DC Blocking Voltage @T <sub>A</sub> = 100°C  |                                   | 500         |          |          |          |          |          |          |      |
| Reverse Recovery Time (Note 1)  | t <sub>rr</sub>                   | 35          |          |          | 50       |          |          |          | nS   |
| Typical Junction Capacitance (Note 2)   | C <sub>j</sub>                    | 80          |          |          | 60       |          |          |          | pF   |
| Operating and Storage Temperature Range   | T <sub>j</sub> , T <sub>STG</sub> | -65 to +150 |          |          |          |          |          |          | °C   |

Note: 1. Measured with I<sub>F</sub> = 0.5A, I<sub>R</sub> = 1.0A, I<sub>RR</sub> = 0.25A.  
2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

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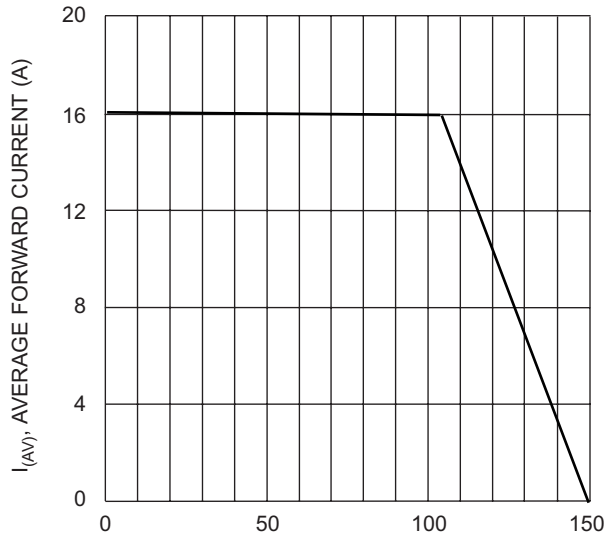


Fig. 1 Forward Current Derating Curve

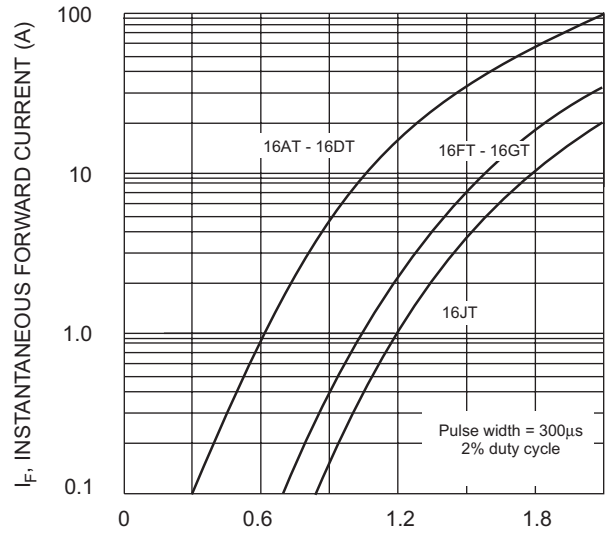


Fig. 2 Typical Forward Characteristics

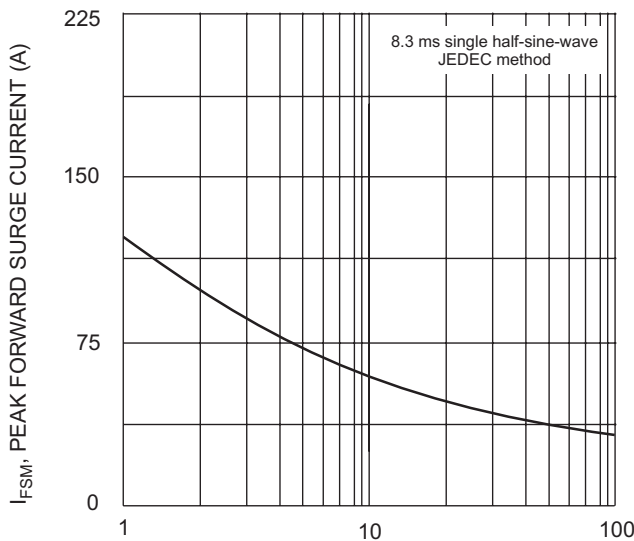


Fig. 3 Maximum Non-Repetitive Surge Current

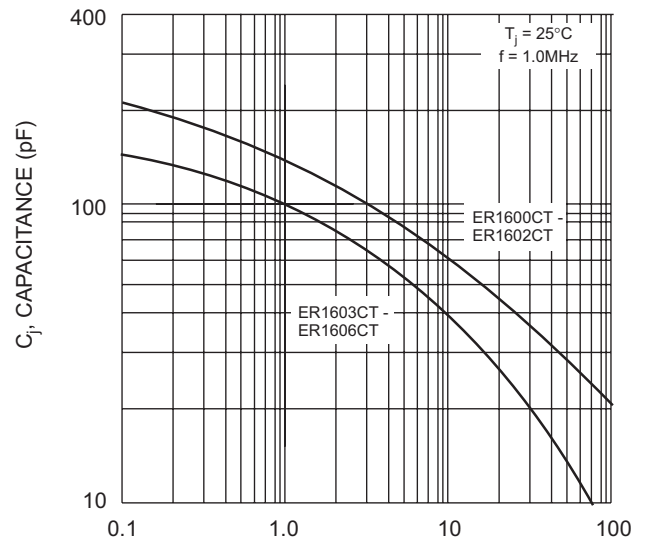
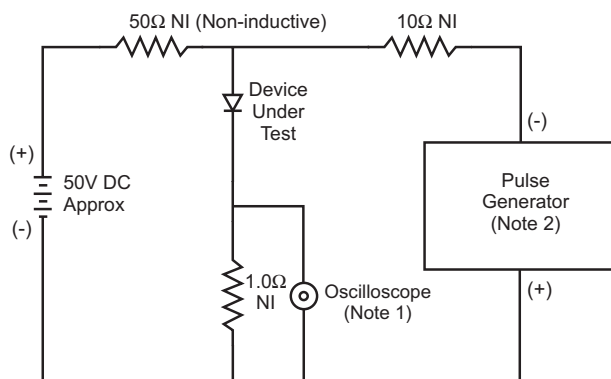
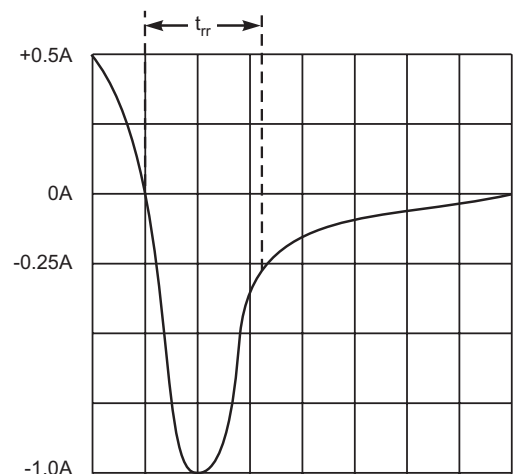


Fig. 4 Typical Junction Capacitance



Notes:  
1. Rise Time = 7.0ns max. Input Impedance = 1.0MΩ, 22pF.  
2. Rise Time = 10ns max. Input Impedance = 50Ω.



Set time base for 5/10ns/cm

Fig. 5 Reverse Recovery Time Characteristic and Test Circuit

**TECHNICAL DATA**

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